

SANYO	No.4756	2SC4923
	NPN Triple Diffused Planar Silicon Transistor Very High-Definition CRT Display Horizontal Deflection Output Applications	

Features

- High speed (t_f typ. = 100ns).
- High reliability (Adoption of HVP process).
- High breakdown voltage ($V_{CBO} = 1500V$).
- Adoption of MBIT process.

Absolute Maximum Ratings at $T_a = 25^\circ C$

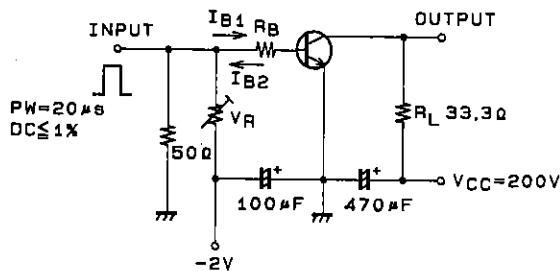
			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	800	V
Emitter-to-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	8	A
Collector Current (Pulse)	I_{CP}	25	A
Collector Dissipation	P_C	3.0	W
		70	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

$T_c = 25^\circ C$

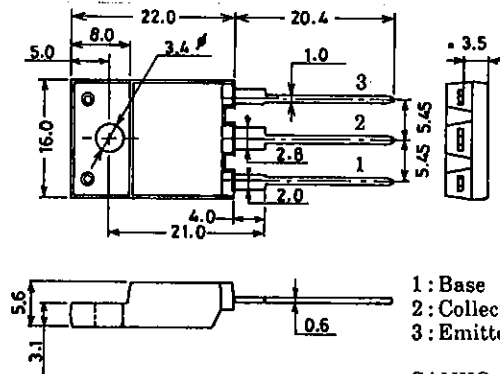
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V, I_E = 0$			10	μA
	I_{CES}	$V_{CE} = 1500V, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 6A, I_B = 1.5A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 6A, I_B = 1.5A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1A$	8			
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 6A$	4		8	
Storage Time	t_{stg}	$I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$			3.0	μs
Fall Time	t_f	$I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$	0.1	0.2		μs

Switching Time Test Circuit

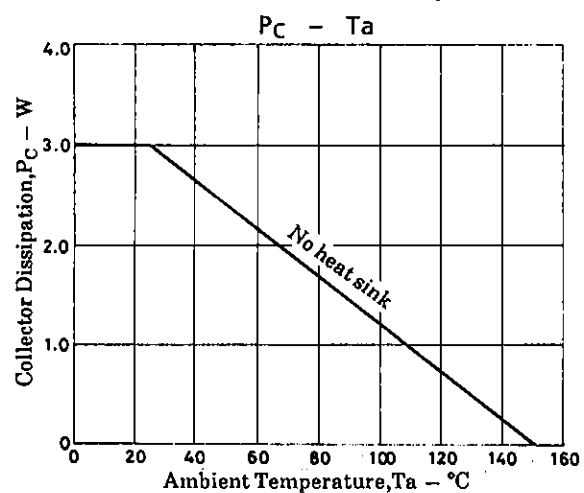
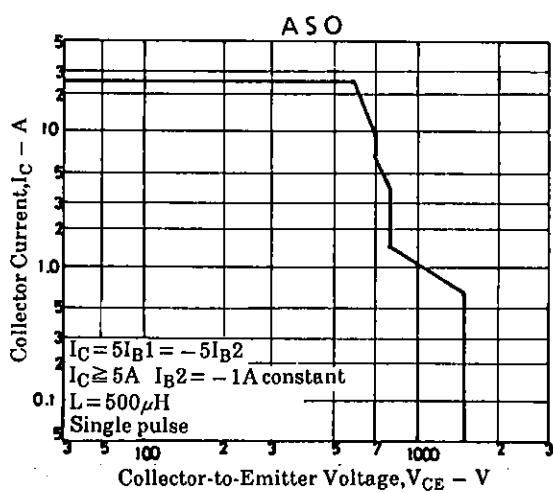
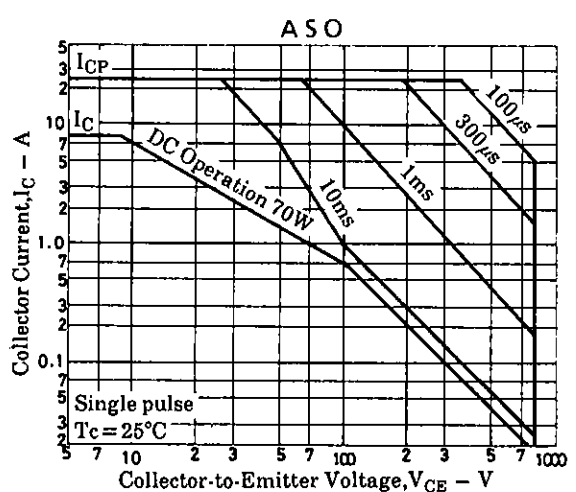
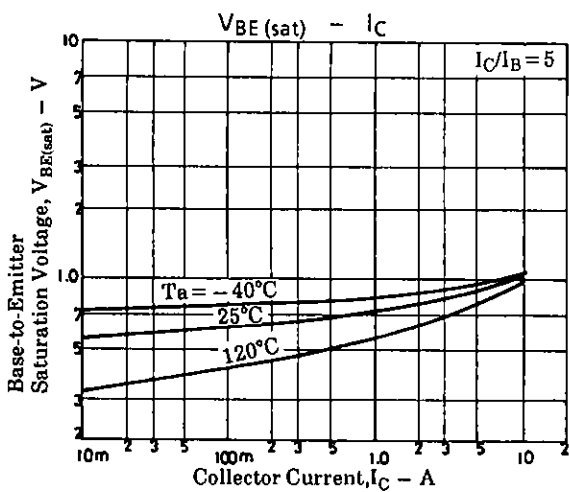
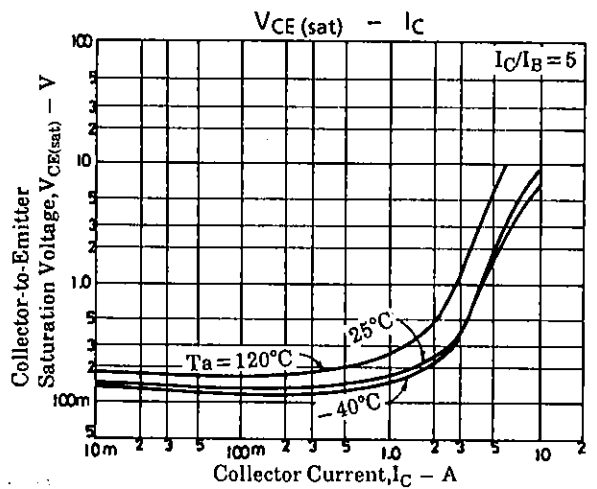
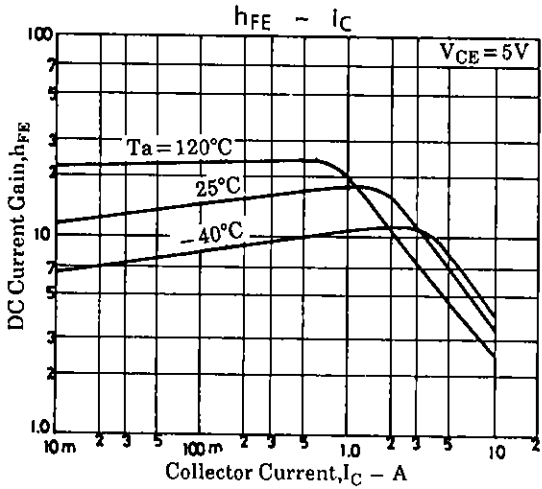
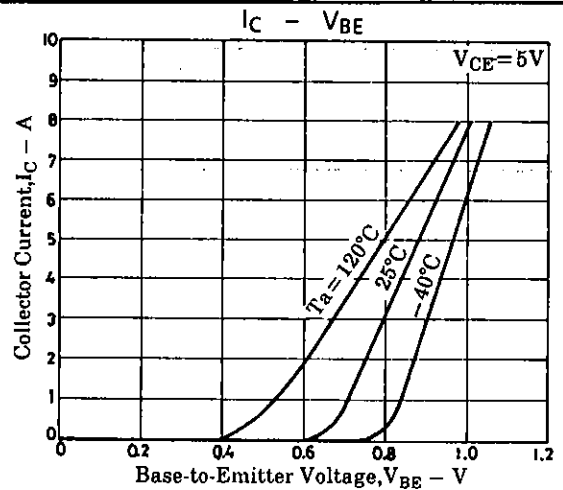
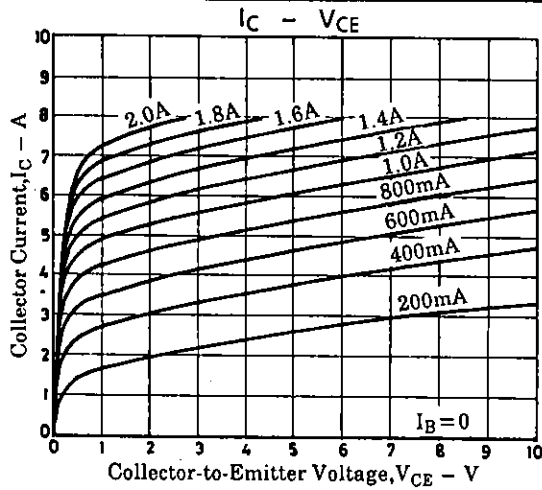


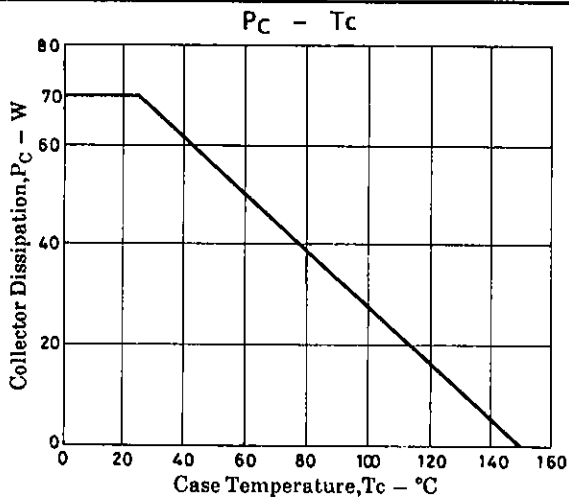
Package Dimensions 2039C
(unit: mm)



SANYO: TO-3PML

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